

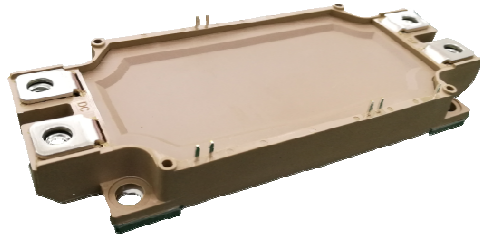
# YZPST-450B170E53

## IGBT Power Module

$V_{CE}=1700V$   $I_C=450A$

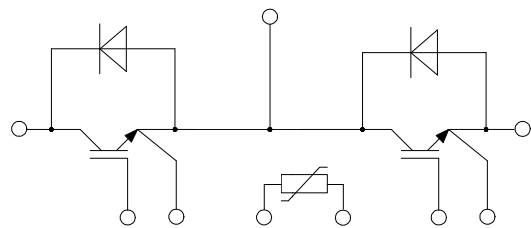
### Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)



### Features

- Low  $V_{ce(sat)}$  with SPT+ IGBT technology
- $V_{ce(sat)}$  with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- High short circuit capability(10us)
- Low inductance module structure
- Maximum junction temperature 175°C



Equivalent Circuit Schematic

### ● Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_c =1mA, T_{vj}=25^{\circ}C$	1700	V
Continuous Collector Current	$I_c$	$T_c=100^{\circ}C$	450	A
Peak Collector Current	$I_{CRM}$	$t_p=1ms$	900	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25^{\circ}C$	$\pm 20$	V
Total Power Dissipation (IGBT-inverter)	$P_{tot}$	$T_c=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	3260	W

**● IGBT Characteristics**

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=24mA, T_{vj}=25^{\circ}C$	5.4	6.2	7.4	V
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1700V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=450A, V_{GE}=15V, T_{vj}=25^{\circ}C$		2.40	2.75	V
		$I_C=450A, V_{GE}=15V, T_{vj}=125^{\circ}C$		2.80		V
		$I_C=450A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.90		V
Gate Charge	$Q_G$			2.70		uC
Input Capacitance	$C_{ies}$			30.0		nF
Output Capacitance	$C_{oes}$	$V_{CE}=25V, V_{GE}=0V, f=1MHz, T_{vj}=25^{\circ}C$		1.65		nF
Reverse Transfer Capacitance	$C_{res}$			1.08		nF
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=450A, V_{CE}=900V, V_{GE}=\pm 15V, R_G=3.3\Omega, T_{vj}=25^{\circ}C$		510		ns
Rise Time	$t_r$			180		ns
Turn-off Delay Time	$t_{d(off)}$			620		ns
Fall Time	$t_f$			185		ns
Energy Dissipation During Turn-on Time	$E_{on}$			126		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			89.0		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=450A, V_{CE}=900V, V_{GE}=\pm 15V, R_G=3.3\Omega, T_{vj}=125^{\circ}C$		512		ns
Rise Time	$t_r$			190		ns
Turn-off Delay Time	$t_{d(off)}$			712		ns
Fall Time	$t_f$			350		ns
Energy Dissipation During Turn-on Time	$E_{on}$			162		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			125		mJ

Turn-on Delay Time	$t_{d(on)}$	$I_C = 450\text{ A}$ $V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 3.3\Omega$ $T_{vj} = 150^\circ\text{C}$	515		ns
Rise Time	$t_r$		200		ns
Turn-off Delay Time	$t_{d(off)}$		730		ns
Fall Time	$t_f$		430		ns
Energy Dissipation During Turn-on Time	$E_{on}$		175		mJ
Energy Dissipation During Turn-off Time	$E_{off}$		130		mJ
SC Data	$I_{sc}$	$T_p \leq 10\mu\text{s}, V_{GE} = 15\text{ V},$ $T_{vj} = 150^\circ\text{C}, V_{cc} = 1000\text{ V},$ $V_{CEM} \leq 1700\text{ V}$	1450		A

### ● Diode Characteristics

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode DC Forward Current	$I_F$	$T_c = 100^\circ\text{C}$		450		A
Diode Peak Forward Current	$I_{FRM}$	$t_p = 1\text{ ms}$		900		A
Forward Voltage	$V_F$	$I_F = 450\text{ A}, T_{vj} = 25^\circ\text{C}$		1.85		V
		$I_F = 450\text{ A}, T_{vj} = 125^\circ\text{C}$		1.92		V
		$I_F = 450\text{ A}, T_{vj} = 150^\circ\text{C}$		1.90		V
Recovered Charge	$Q_{rr}$	$I_F = 450\text{ A}$		110		$\mu\text{C}$
Peak Reverse Recovery Current	$I_{rr}$	$V_R = 900\text{ V}$ $-di_F/dt = 2500\text{ A}/\mu\text{s}$		348		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj} = 25^\circ\text{C}$		64.2		mJ
Recovered Charge	$Q_{rr}$	$I_F = 450\text{ A}$		160		$\mu\text{C}$
Peak Reverse Recovery Current	$I_{rr}$	$V_R = 900\text{ V}$ $-di_F/dt = 2500\text{ A}/\mu\text{s}$		394		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj} = 125^\circ\text{C}$		94.4		mJ
Recovered Charge	$Q_{rr}$	$I_F = 450\text{ A}$		176		$\mu\text{C}$
Peak Reverse Recovery Current	$I_{rr}$	$V_R = 900\text{ V}$ $-di_F/dt = 2500\text{ A}/\mu\text{s}$		410		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj} = 150^\circ\text{C}$		103.2		mJ

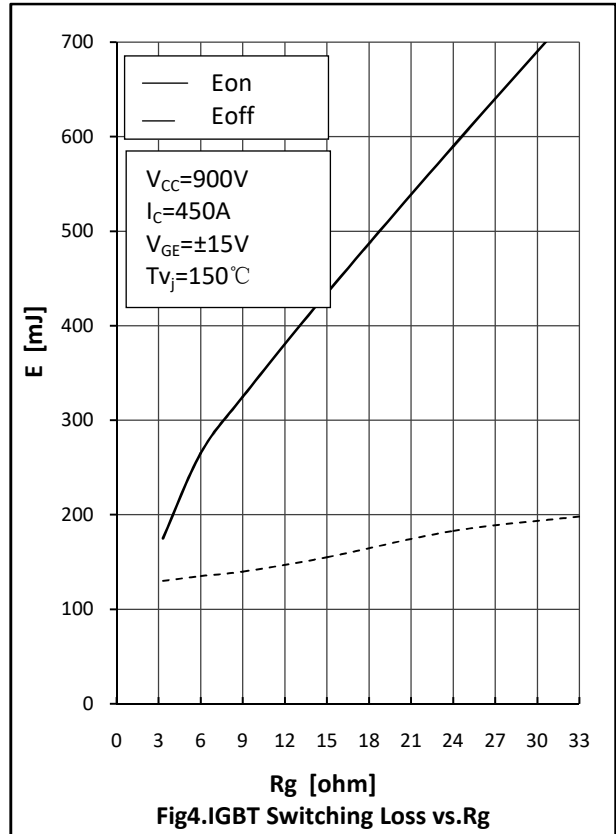
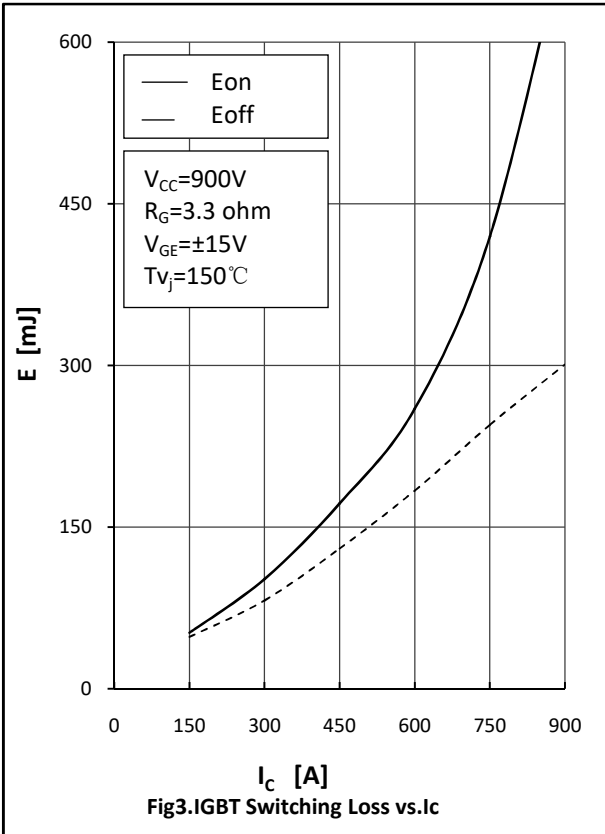
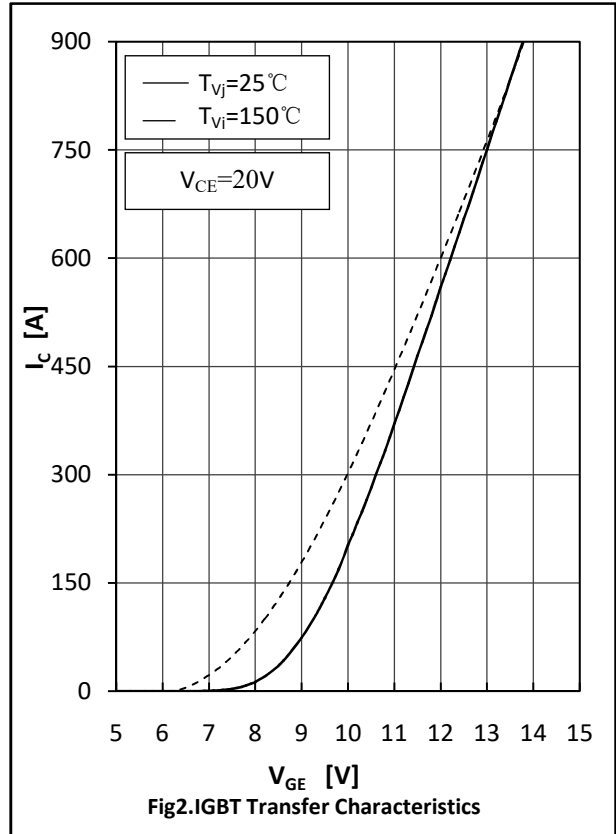
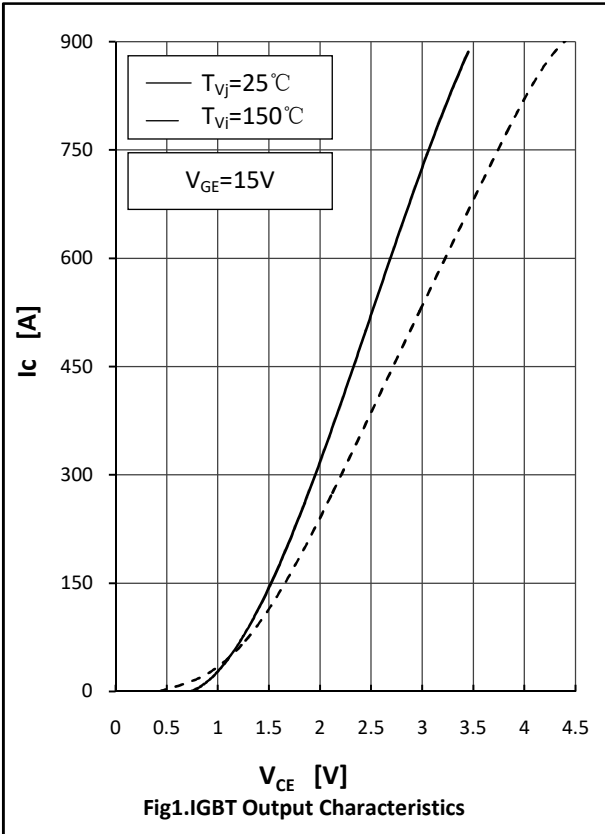
**● NTC-Thermistor**
**Characteristic values**

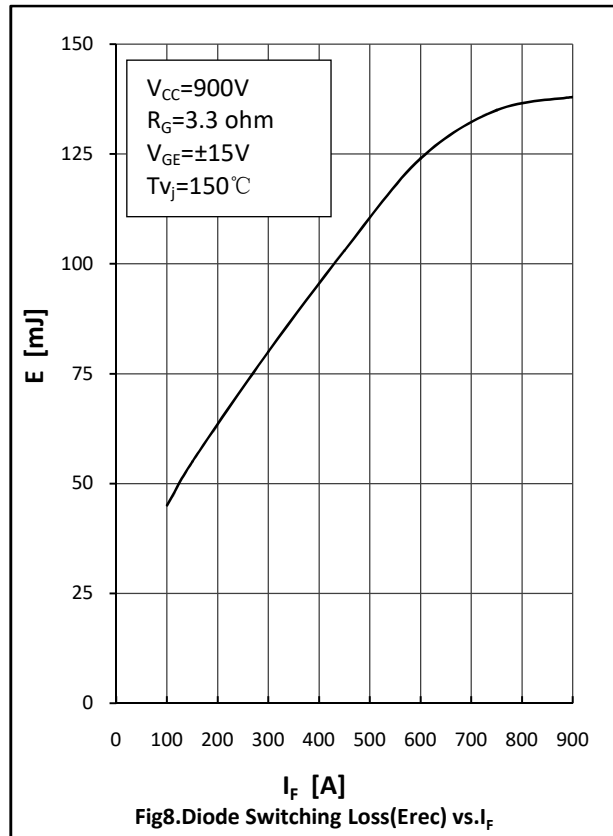
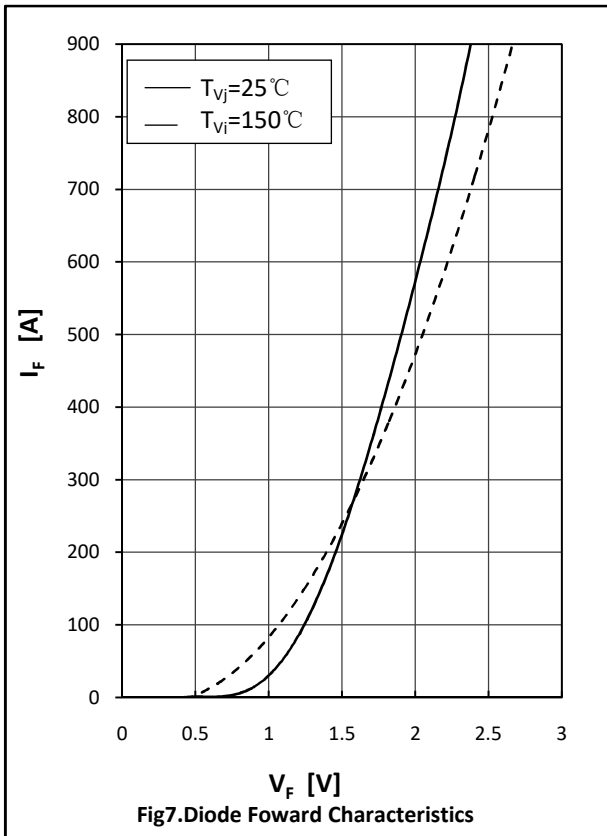
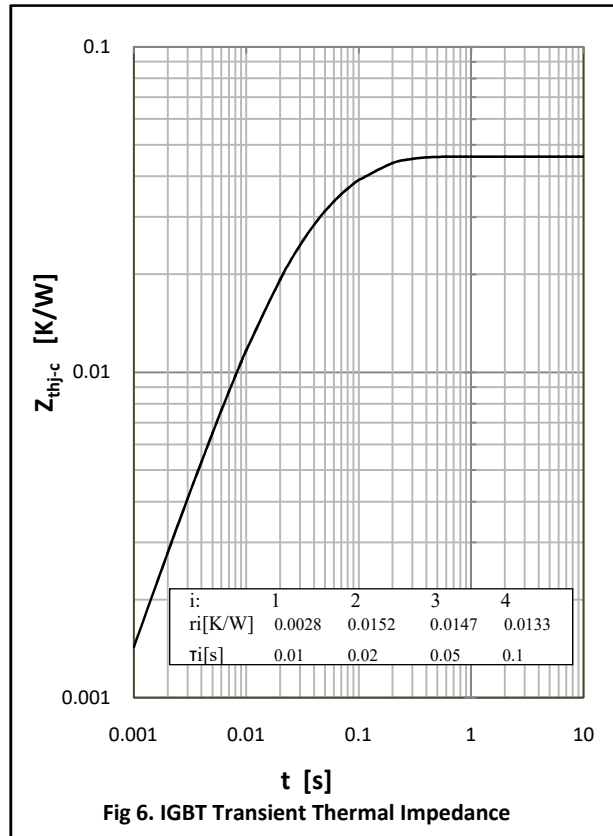
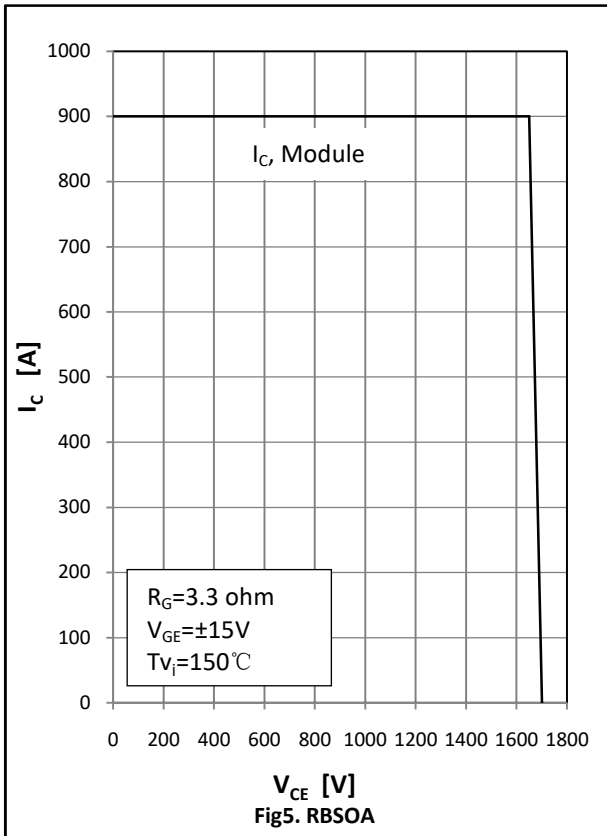
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R <sub>25</sub>			5.0		k Ω
Deviation of R100	ΔR/R	T <sub>C</sub> =100,R <sub>100</sub> =493.3 Ω	-5		5	%
Power Dissipation	P <sub>25</sub>			20.0		mW
B-value	B <sub>25/50</sub>	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15K))]$		3375		K

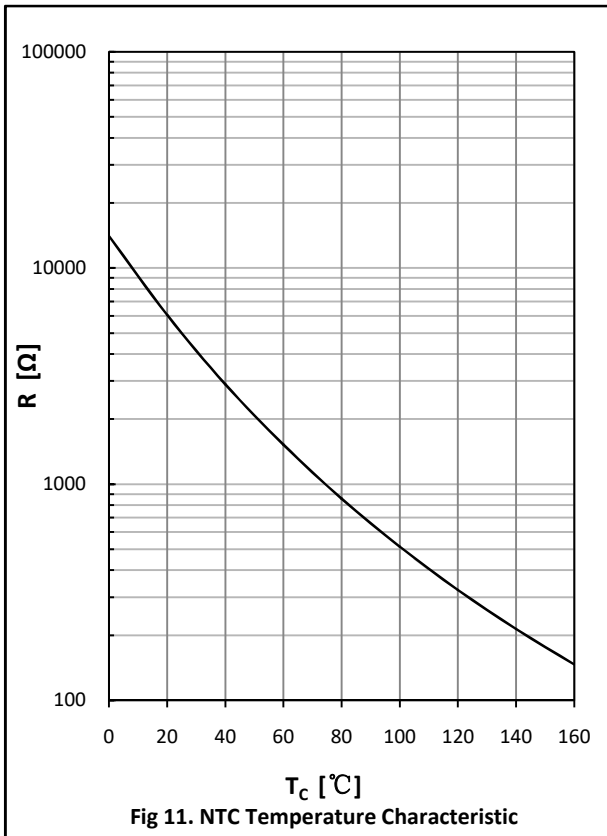
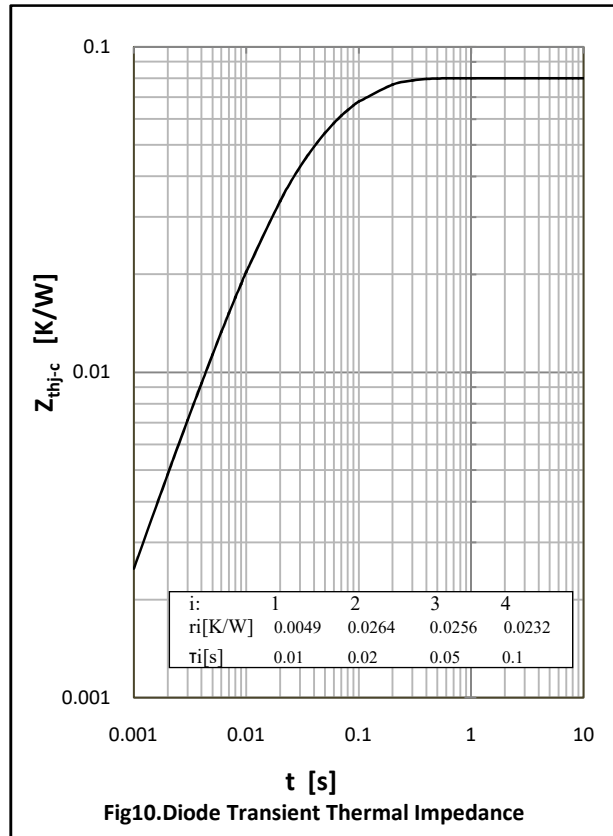
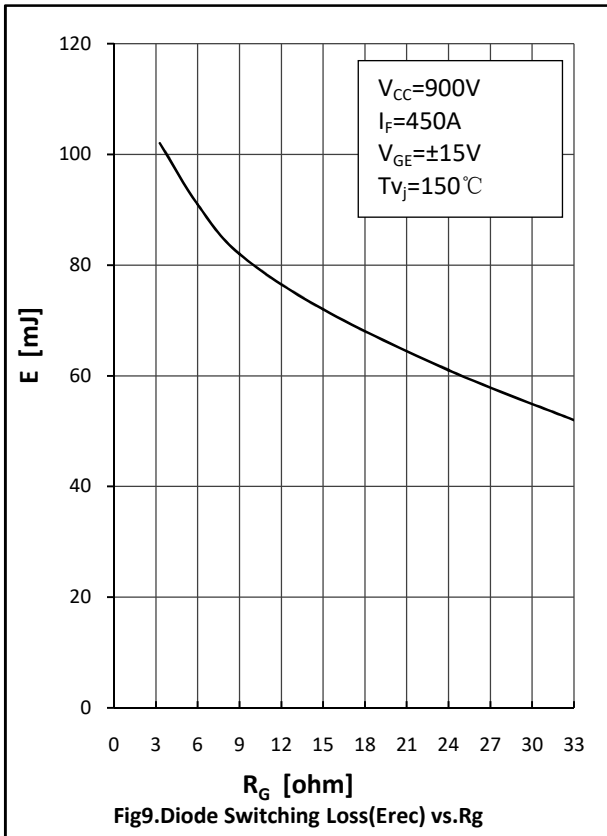
**● Module Characteristics**

 T<sub>C</sub>=25°C unless otherwise specified

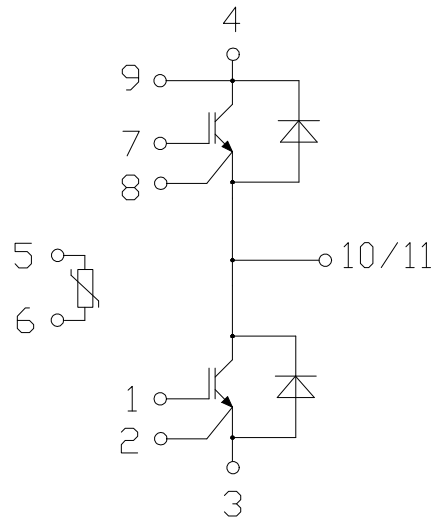
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	V <sub>isol</sub>	t=1min,f=50Hz	4000			V
Maximum Junction Temperature	T <sub>jmax</sub>				175	°C
Operating Junction Temperature	T <sub>vj op</sub>		-40		150	°C
Storage Temperature	T <sub>stg</sub>		-40		125	°C
Stray Inductance	L <sub>CE</sub>			20		nH
Module Lead Resistance ,Terminal to Chip	R <sub>CC+EE'</sub>			1.1		m Ω
Junction-to Case	R <sub>θjc</sub>	per IGBT			0.046	K/W
		per Diode			0.080	
Case to Sink (Conductive grease applied)	R <sub>θcs</sub>	per IGBT		0.028		K/W
		per Diode		0.049		
		per Module		0.009		
Module Electrodes Torque	M <sub>t</sub>	Recommended(M6)	3.0		6.0	N·m
Module-to-Sink Torque	M <sub>s</sub>	Recommended(M5)	3.0		6.0	N·m
Weight of Module	G			350		g







● Circuit Diagram



● Package Dimensions

Dimensions in Millimeters

